

**Amendments to the Claims**

The following listing of the claims replaces all previous amendments and listings of the claims.

1. (Currently Amended) A wet treatment method useful in at least one of a chemical processing step and a rinsing step performed upon fabrication of semiconductor devices, which comprises a sub-step in which:

a substrate under treatment is treated with a desired liquid while causing said substrate to revolve around an axis of rotation outside said substrate such that said desired liquid flowing on a surface of said substrate is maintained flowing under a centrifugal force greater than gravitation, the surface of the substrate disposed on a horizontal plane perpendicular to the axis of rotation, and

said substrate is treated while supplying a fresh liquid of the same kind as said desired liquid at a flow rate at least equal to a discharge rate of said desired liquid only in a direction ~~conforming with that of said centrifugal force or with that of a flow of said desired liquid flowing on said surface of said substrate under said centrifugal force~~ perpendicular to the axis of rotation,

whereby said substrate is evenly treated at said surface thereof with said desired liquid while avoiding development of such a situation that flows of said desired liquid run against each other on said surface of said substrate or a flow of said desired liquid stagnates on said surface of said substrate.

2. (Previously Presented) A wet treatment method according to claim 1, wherein said desired liquid has such a high viscosity and/or adhesion as tending to allow said desired liquid to remain on said surface of said substrate, or contains an organic substance.

3. (Original) A wet treatment method according to claim 1, wherein said sub-step is conducted in an initial stage of at least one of said chemical processing step and said rinsing

step.

4. (Previously Presented) A wet treatment method according to claim 3, wherein said wet treatment method is used in said rinsing step for a chemical employed in said chemical processing step; and said chemical is one having such a high viscosity and/or adhesion as tending to allow said desired liquid to remain on said surface of said substrate, one containing an organic substance, or one having such a property that its etching rate quickly increases when mixed with water.

5. (Original) A wet treatment method according to claim 2, wherein said wet treatment method is used in said rinsing step for a chemical employed in said chemical processing step; and said chemical is a solution of at least one of amines and ammonium fluoride dissolved as an effective component in an organic solvent or a water-containing organic solvent.

6. (Previously Presented) A wet treatment method according to claim 1, wherein said desired liquid employed in said sub-step is pure water.

7.-11. (Canceled)

12. (Currently Amended) A method of treating a substrate, comprising:  
rotating the substrate about an axis disposed apart from the substrate, a surface of the substrate disposed on a horizontal plane perpendicular to the axis; and  
supplying a liquid to treat the surface of the substrate in a direction only ~~along a direction of centrifugal force on the substrate during the rotation~~ perpendicular to the axis.

13. (Currently Amended) The method according to claim 12, wherein rotation comprises rotating the substrate such that ~~the~~ a centrifugal force is greater than a gravitational force.

14. (Currently Amended) The method according to claim 12, wherein supplying comprises supplying the liquid at a rate at least equal to a rate of removal of the liquid from the substrate due to ~~the~~ a centrifugal force.

15. (Currently Amended) The method according to claim 12, wherein rotating comprises rotating the substrate such that the supplied liquid flows in a direction of liquid flow from the substrate due to ~~the~~ a centrifugal force.

16. (Previously Presented) The method according to claim 15, wherein the liquid comprises water.

17. (Previously Presented) The method according to claim 16, wherein the liquid comprises chemical etchant.